TOSHIBA GTR Module Silicon N Channel IGBT

MG150Q2YS51

High Power Switching Applications Motor Control Applications

• High input impedance

• High speed : $t_f = 0.3 \mu s$ (Max)

@Inductive Load

• Low saturation voltage

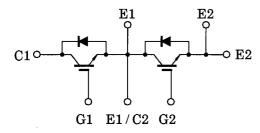
 $: V_{CE (sat)} = 3.6V (Max)$

• Enhancement-mode

• Includes a complete half bridge in one package.

• The electrodes are isolated from case.

Equivalent Circuit



Maximum Ratings (Ta = 25°C)

| Unit: mm |
|---|
| 3-M5 4-FAST-ON-TAB # 110 28 ± 0.6 28 ± 0.6 28 ± 0.6 28 ± 0.8 93 ± 0.3 108 ± 0.8 |
| 3±0.3 3±0.3 3±0.3 21.5±0.6 41 54±0.6 54±0.6 9 9 9 9 9 9 9 9 9 9 9 9 9 9 9 9 9 9 9 |
| JEDEC — |
| EIAJ — |
| TOSHIBA 2-109C4A |

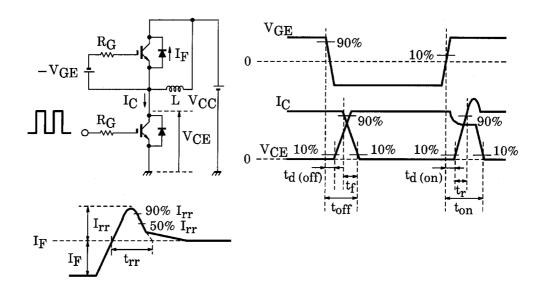
Weight: 430g

| Characteristic | | Symbol | Rating | Unit | |
|---|-----|---|---------------------|------|--|
| Collector-emitter voltage | | V _{CES} | 1200 | V | |
| Gate-emitter voltage | | V _{GES} | ±20 | V | |
| Collector current | DC | I _C (25°C / 80°C) | 200 / 150 | А | |
| | 1ms | I _{CP} (25°C / 80°C) 400 / 300 | | | |
| Forward current | DC | IF | 150 | A | |
| | 1ms | I _{FM} | 300 | | |
| Collector power dissipation (Tc = 25°C) | | PC | 1250 | W | |
| Junction temperature | | Tj | 150 | °C | |
| Storage temperature range | | T _{stg} | − 40 ~ 125 | °C | |
| Isolation voltage | | V _{Isol} | 2500 (AC 1 min.) | V | |
| Screw torque (Terminal / mounting) | | _ | 3/3 | N·m | |

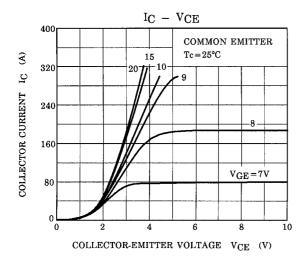
Electrical Characteristics (Ta = 25°C)

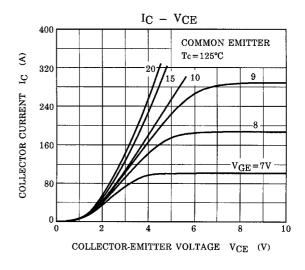
| Chara | acteristic | Symbol | Test Condition | | Min | Тур. | Max | Unit |
|--------------------------------------|--|-----------------------|--|------------------------|-----|------|------|------|
| Gate leakage currer | e leakage current I _{GES} V _{GE} = ±20V, V _{CE} = 0 | | = 0 | _ | _ | ±500 | nA | |
| Collector cut-off curr | off current I_{CES} $V_{CE} = 1200V, V_{GE} = 0$ | | _{SE} = 0 | _ | _ | 2.0 | mA | |
| Gate-emitter cut-off | voltage | V _{GE} (off) | I _C = 150mA, V _{CE} = 5V | | 3.0 | _ | 6.0 | V |
| Collector-emitter saturation voltage | | V _{CE} (sat) | I _C = 150A, V _{GE} = 15V | T _j = 25°C | _ | 2.8 | 3.6 | V |
| | | | | T _j = 125°C | _ | 3.1 | 4.0 | |
| Input capacitance | | C _{ies} | V _{CE} = 10V, V _{GE} = 0, f = 1MHz | | _ | 18.0 | _ | nF |
| Switching time | Turn-on delay time | t _{d(on)} | | | _ | 0.05 | _ | , µs |
| | Rise time | t _r | Inductive load V _{CC} = 600V | | _ | 0.05 | _ | |
| | Turn-on time | t _{on} | I _C = 150A | | _ | 0.2 | _ | |
| | Turn-off delay time | t _{d(off)} | $V_{GE} = \pm 15V$ $R_G = 5.6\Omega$ | | _ | 0.5 | _ | |
| | Fall time | t _f | | (Note 1) | _ | 0.1 | 0.3 | |
| | Turn-off time | t _{off} | | | _ | 0.6 | _ | |
| Forward voltage | orward voltage V_F $I_F = 150A, V_{GE} = 0$ | | 0 | _ | 2.4 | 3.5 | V | |
| Reverse recovery time | | t _{rr} | I_F = 150A, V_{GE} = -10V di / dt = 700A / μ s (Note 1) | | _ | 0.1 | 0.25 | μs |
| Thermal resistance | | R _{th (j-c)} | Transistor stage | | _ | _ | 0.1 | °C/W |
| | | | Diode stage | | _ | _ | 0.24 | |

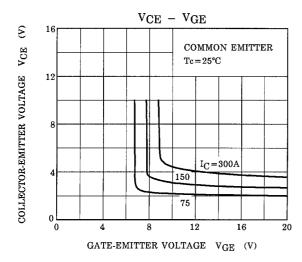
Note 1: Switching time and reverse recovery time test circuit & timing chart

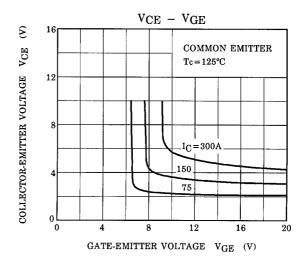


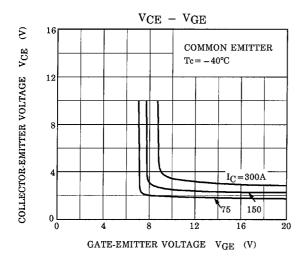
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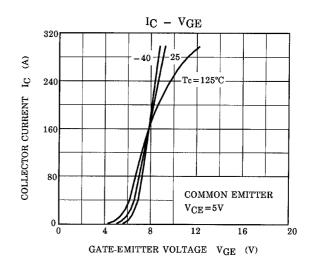


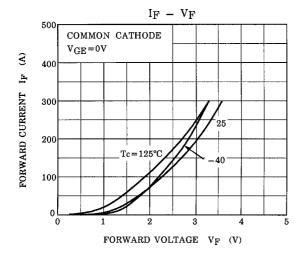


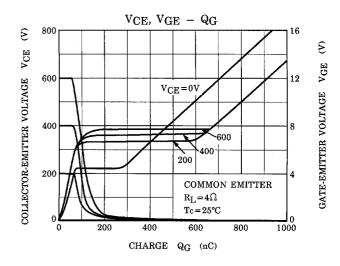


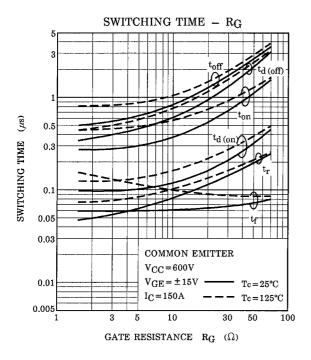


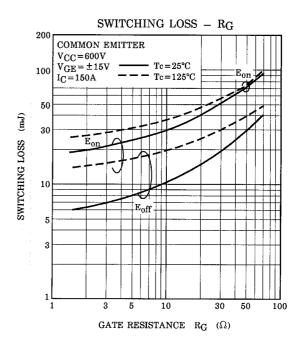




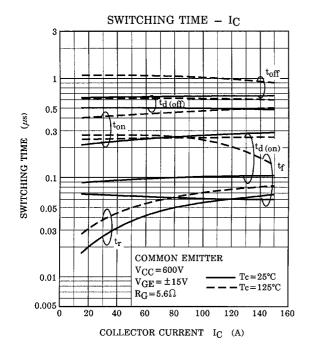


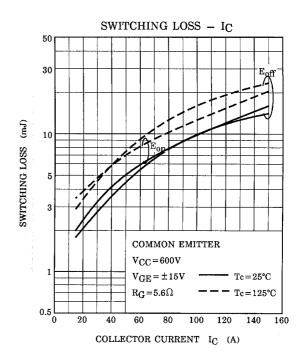


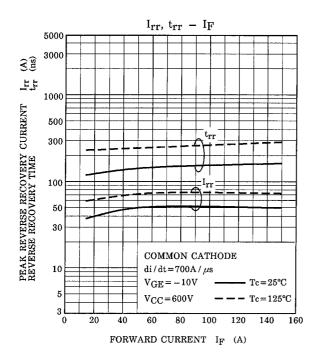


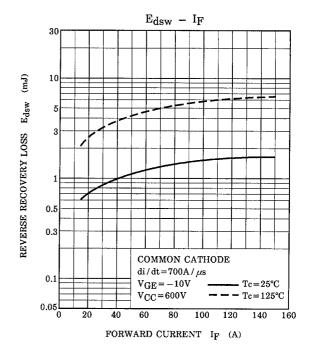


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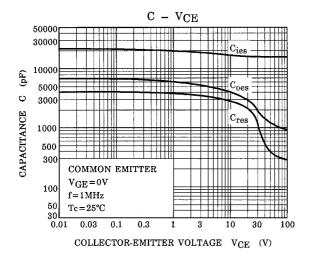


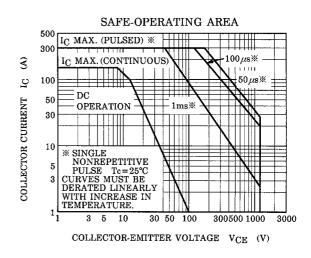


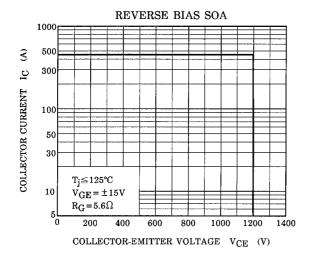


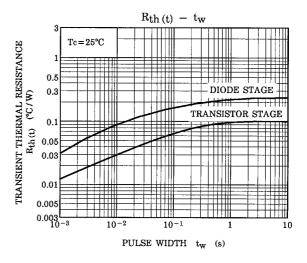


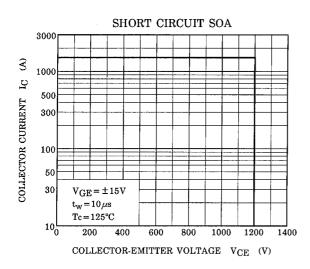
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